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Method for programming an analog/multi-level flash EEPROM - Patent ...

For analog/**multi-level Flash** EEPROM, the cell V_t is programmed with different threshold at 3 volts, and an **over-program** specification at 0.5 volts. ...

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Multi-level nonvolatile semiconductor memory device - Patent 5986929

Thus, in the write and verify operations of "10" and "01" data, occurrence of **over-program** of "00" data can be prevented. In the **multi-level nonvolatile** ...

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(WO/2006/110395) SPLIT GATE MULTI-BIT MEMORY CELL

Accordingly, there is a need for **multi-bit flash** memory devices which require 1) **over program**/erase cycling. The physically isolated first and second ...

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(WO/2005/013283) DETECTING OVER PROGRAMMED MEMORY CELLS AFTER ...

A method according to claim 1, wherein: said one or more **multi-state** ... said first **multi-state** storage element for edges of one or more **over program** ranges ...

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Test Strategies on Non Volatile Memories

with an example on a high density NOR-Flash **multi-level** cell **Over-program**/low R on set state (PCM). bitline. bitline ...

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A Novel Soft-Program for a Narrow Erased State V_t Distribution ...

application of more-than-2-bit MLC **flash** memories. [DOI: 10.1143/JJAP.42.2044].

KEYWORDS: **multilevel** cell, soft-program, read disturbance, **over-program**, ...
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[PDF] **Flash Memory Technology**

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Most of the major **flash** companies are working to develop their version of a **multi-level** cell **flash** device. The goal of this device is to store information ...

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